

SOT-23 Formed SMD Package

**BSR19
BSR19A**

SILICON N-P-N HIGH-VOLTAGE TRANSISTORS

N-P-N high-voltage small-signal transistors

Marking

BSR19 = U35

BSR19A = U36

PACKAGE OUTLINE DETAILS

ALL DIMENSIONS IN *mm*

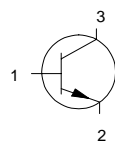


Pin configuration

1 = BASE

2 = EMITTER

3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

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Collector-base voltage (open emitter)	V_{CB0} max.	160 180 V
Collector-emitter voltage (open base)	V_{CE0} max.	140 160 V
Collector current	I_C max.	600 600 mA
Total power dissipation up to $T_{amb} = 25\text{ }^{\circ}\text{C}$	P_{tot} max.	250 250 mW
Junction temperature	T_j max.	150 150 $^{\circ}\text{C}$
Collector-emitter saturation voltage $I_C = 50\text{ mA}; I_B = 5\text{ mA}$	V_{CEsat} max.	0,25 0,20 V
D.C. current gain $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE} min.	60 80

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RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	V_{CB0}	max.	160	180 V
Collector-emitter voltage (open base)	V_{CE0}	max.	140	160 V
Emitter-base voltage (open collector)	V_{EB0}	max.	6	V
Collector current	I_C	max.	600	mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	250	mW
Junction temperature	T_j	max.	150	$^\circ\text{C}$
Storage temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

THERMAL RESISTANCE

From junction to ambient	$R_{th\ j-a}$	=	500	K/W
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CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

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Collector cut-off current				
$I_E = 0; V_{CB} = 100\text{ V}$	I_{CBO}	max.	100	nA
$I_E = 0; V_{CB} = 120\text{ V}$	I_{CBO}	max.		50 nA
$I_E = 0; V_{CB} = 100\text{ V}; T_{amb} = 100^\circ\text{C}$	I_{CBO}	max.	100	mA
$I_E = 0; V_{CB} = 120\text{ V}; T_{amb} = 100^\circ\text{C}$	I_{CBO}	max.		50 mA
Emitter cut-off current				
$I_C = 0; V_{EB} = 4,0\text{ V}$	I_{EBO}	max.	50	50 nA
Breakdown voltages				
$I_C = 1,0\text{ mA}; I_B = 0$	$V_{(BR)CEO}$	min.	140	160 V
$I_C = 100\text{ mA}; I_E = 0$	$V_{(BR)CBO}$	min.	160	180 V
$I_C = 0; I_E = 10\text{ mA}$	$V_{(BR)EBO}$	min.	6,0	6,0 V
Saturation voltages				
$I_C = 10\text{ mA}; I_B = 1,0\text{ mA}$	V_{CEsat}	max.	0,15	0,15 V
	V_{BEsat}	max.	1,0	1,0 V
$I_C = 50\text{ mA}; I_B = 5,0\text{ mA}$	V_{CEsat}	max.	0,25	0,20 V
	V_{BEsat}	max.	1,2	1,0 V
D.C. current gain				
$I_C = 1,0\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	60	80
$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	60	80
		max.	250	250
$I_C = 50\text{ mA}; V_{CE} = 5\text{ V}$	h_{FE}	min.	20	30
Small-signal current gain				
$I_C = 1,0\text{ mA}; V_{CE} = 10\text{ V}; f = 1\text{ kHz}$	h_{fe}	min.	50	50
		max.	200	200
Output capacitance at $f = 1\text{ MHz}$				
$I_E = 0; V_{CB} = 10\text{ V}$	C_o	max.	6	6 pF

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				BSR19	BSR19A
Input capacitance at $f = 1 \text{ MHz}$ $I_C = 0; V_{EB} = 0,5 \text{ V}$		C_i	max.	30	30 pF
Transition frequency at $f = 100 \text{ MHz}$ $I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}$		f_T	min.	100	100 MHz
			max.	300	300 MHz
Noise figure at $R_S = 1 \text{ kW}$ $I_C = 250 \text{ mA}; V_{CE} = 5 \text{ V}; f = 10 \text{ Hz to } 15,7 \text{ kHz}$		F	max.	10	8 dB

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